

Package: QFN, 6 mmx6 mm

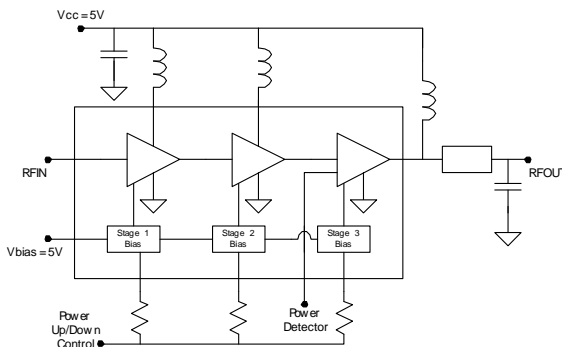


Product Description

RFMD's SZM-2166Z is a high linearity class AB Heterojunction Bipolar Transistor (HBT) amplifier housed in a low-cost surface-mountable plastic Q-FlexN multi-chip module package. This HBT amplifier is made with InGaP on GaAs device technology and fabricated with MOCVD for an ideal combination of low cost and high reliability. This product is specifically designed for 802.16 customer premises equipment (CPE) terminals in the 2.3GHz to 2.7GHz bands. It can run from a 3V to 6V supply. The external output match and bias adjustability allows load line optimization for other applications over narrower bands. It features an output power detector, on/off power control, and high RF overdrive robustness. A 20dB step attenuator feature can be utilized by switching the second stage Power up/down control. This product features a RoHS compliant and Green package with matte finish, designated by the "Z" suffix

Optimum Technology Matching® Applied

- GaAs HBT
- GaAs MESFET
- InGaP HBT
- SiGe BiCMOS
- Si BiCMOS
- SiGe HBT
- GaAs pHEMT
- Si CMOS
- Si BJT
- GaN HEMT
- RF MEMS



Features

- $P_{1dB} = 35\text{ dBm}$ at 6V
- Three Stages of Gain: 37 dB
- 802.11g 54 Mb/s Class AB Performance
- $P_{OUT} = 27\text{ dBm}$ at 2.5% EVM, $V_{CC} = 6\text{V}$, 878 mA
- Active Bias with Adjustable Current
- On-Chip Output Power Detector
- Low Thermal Resistance
- Power Up/Down Control $< 1\mu\text{s}$
- Attenuator step 20dB at $V_{PC2} = 0\text{V}$

Applications

- 802.16 WiMAX Driver or Output Stage
- 802.11b/g WiFi, WiFi
- CPE Terminal Applications

| Parameter | Specification | | | Unit | Condition |
|---------------------------------|---------------|------------|------|-----------------------------|---|
| | Min. | Typ. | Max. | | |
| Frequency of Operation | 2300 | | 2700 | MHz | |
| Output Power at 1dB Compression | | 35 | | dBm | 2.7 GHz |
| Small Signal Gain | 34.5 | 36 | | dB | 2.7 GHz |
| EVM | | 2.5 | | % | 27 dBm Output power EVM 802.11g 54 Mb/s-2.7 GHz |
| Third Order Suppression | | -40 | -35 | dBc | ($P_{OUT} = 23\text{ dBm}$ per tone)-2.7 GHz |
| Noise Figure | | 8.3 | | dB | 2.7 GHz |
| Worst Case Input Return Loss | 10 | 14 | | dB | 2.5 GHz to 2.7 GHz |
| Worst Case Output Return Loss | 13 | 14 | | dB | 2.5 GHz to 2.7 GHz |
| Output Voltage Range | | 0.9 to 1.8 | | V | $P_{OUT} = 10\text{ dBm}$ to 33 dBm |
| Quiescent Current | 615 | 724 | 832 | mA | $V_{CC} = 6\text{V}$ |
| Power Up Control Current | | 4 | | mA | $V_{PC} = 6\text{V}$, $I_{VPC1} + I_{VPC2} + I_{VPC3}$ |
| V_{CC} Leakage Current | | | 100 | μA | $V_{CC} = 6\text{V}$, $V_{PC} = 0\text{V}$ |
| Thermal Resistance | | 12 | | $^{\circ}\text{C}/\text{W}$ | junction - lead |

Test Conditions: 2.5 GHz to 2.7 GHz App circuit, $Z_0 = 50\Omega$, $V_{CC} = 6.0\text{V}$, $I_q = 724\text{ mA}$, $T_{BP} = 30^{\circ}\text{C}$

Absolute Maximum Ratings

| Parameter | Rating | Unit |
|---|-------------|------|
| VC3 Collector Bias Current (I_{VC3}) | 1500 | mA |
| VC2 Collector Bias Current (I_{VC2}) | 500 | mA |
| VC1 Collector Bias Current (I_{VC1}) | 150 | mA |
| ****Device Voltage (V_D) | 9.0 | V |
| Operating Lead Temperature (T_L) | -40 to +85 | °C |
| ****Max CW RF output Power for 50Ω continuous long term operation | 30 | dBm |
| Max CW RF Input Power for 50Ω output load | 26 | dBm |
| Max CW RF Input Power for 10:1 VSWR FR out load | 5 | dBm |
| Max Storage Temperature | -40 to +150 | °C |
| Operating Junction Temperature (T_J) | +150 | °C |
| ESD Human Body Model | Class 1B | |
| Moisture Sensitivity Level | MSL-1 | |



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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****With specified application circuit
 ****No RF Drive

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

$$I_{CQ} V_{CC} < (T_J - T_L) / R_{\theta J-C}$$

Note: I_{CQ} in this equation is for the stage with the highest current

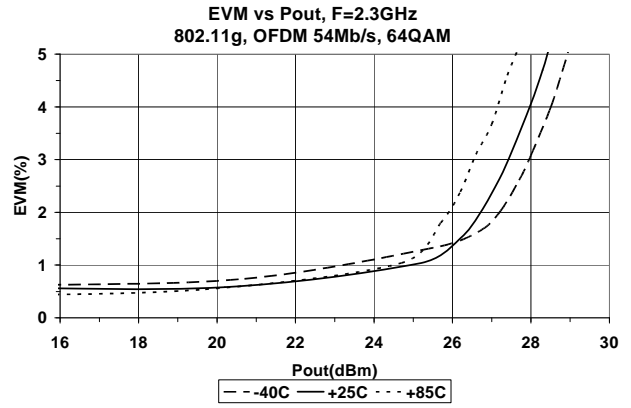
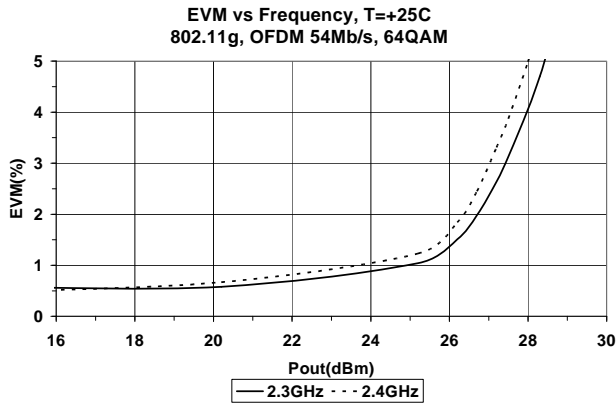
Typical Performance with appropriate app circuit ($V_{CC}=6V$, $I_{CQ}=655mA$, 802.11g 54Mb/s 64QAM)

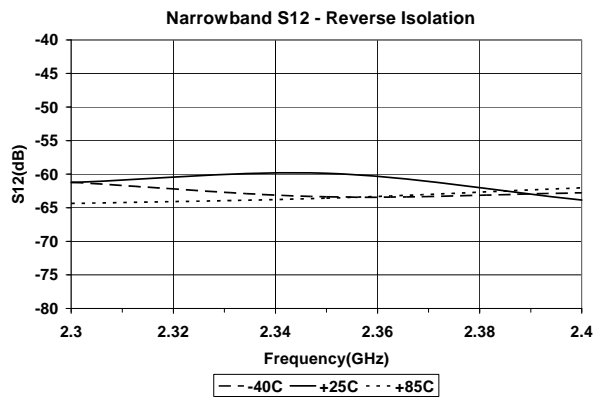
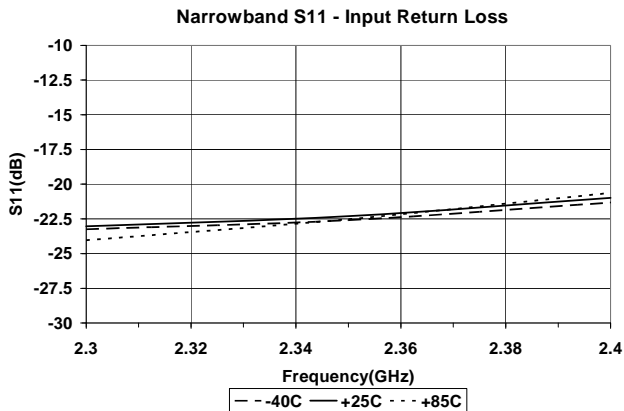
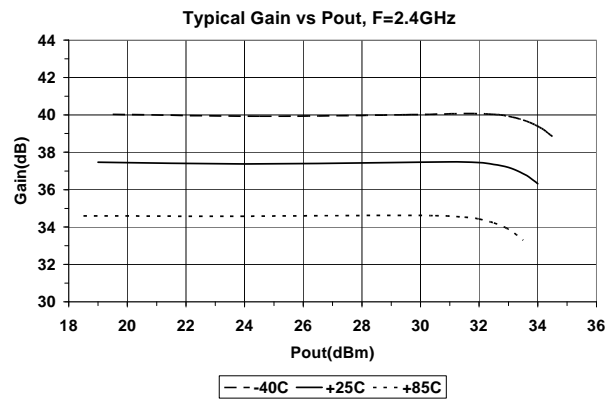
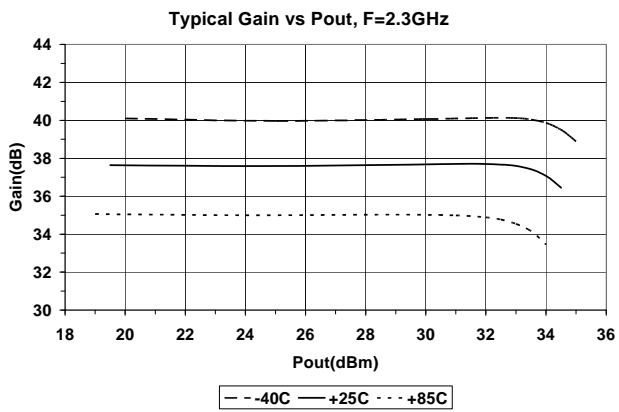
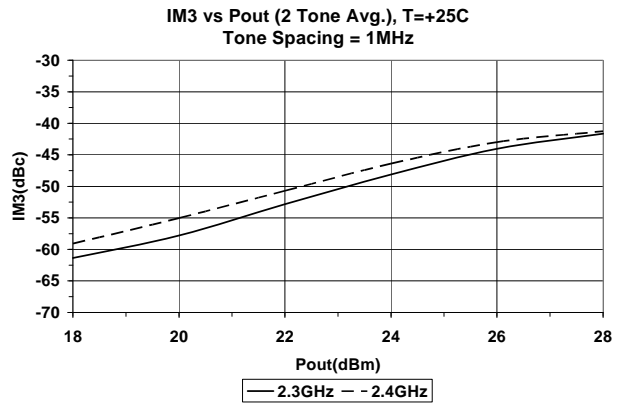
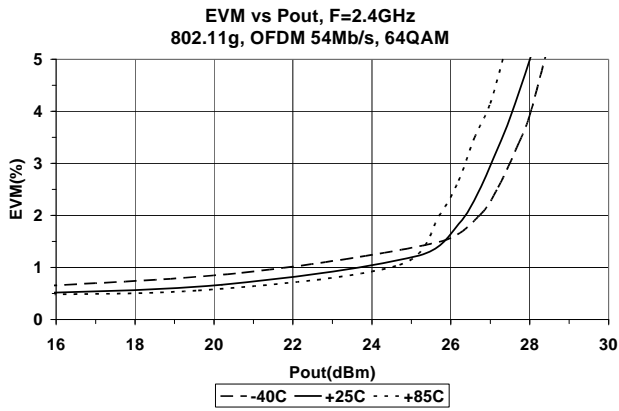
| Parameter | Unit | 2.3 | **2.4 | ***2.5 | ***2.6 | ***2.7 |
|-------------------------------|------|------------------|------------------|------------------|------------------|------------------|
| | | GHz ¹ | GHz ¹ | GHz ² | GHz ² | GHz ² |
| Gain at $P_{OUT}=26dBm$ | dB | 37.5 | 37.5 | 37.5 | 37.0 | 35.0 |
| P_{1dB} | dBm | 34.0 | 34.0 | 35.0 | 35.0 | 35.0 |
| EVM% at 27dBm Output Power | % | 2.3 | 2.9 | 1.7 | 1.7 | 2.5 |
| Current at P_{OUT} 2.5% EVM | mA | 768 | 779 | 900 | 889 | 878 |
| Input Return Loss | dB | 23.0 | 21.0 | 14.0 | 14.0 | 14.0 |
| Output Return Loss | dB | 14.0 | 11.0 | 20.0 | 25.0 | 18.0 |

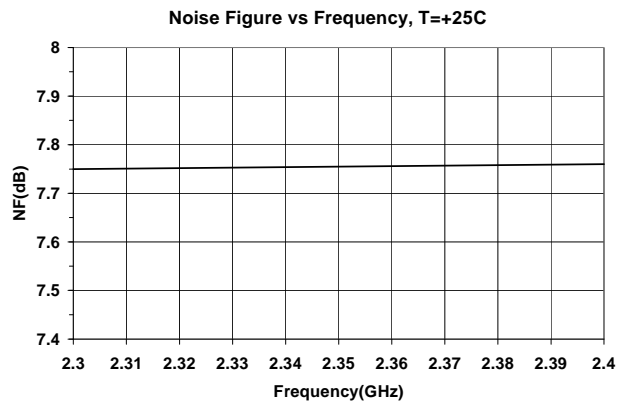
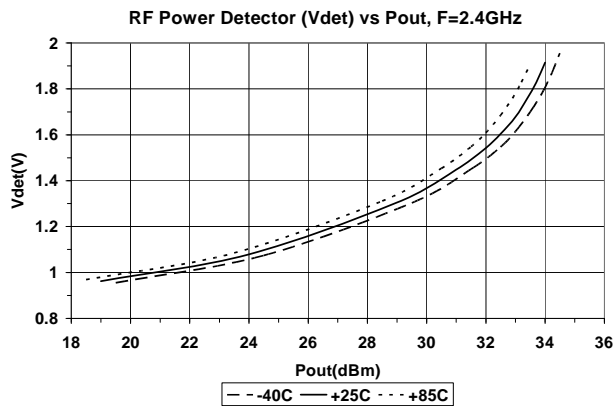
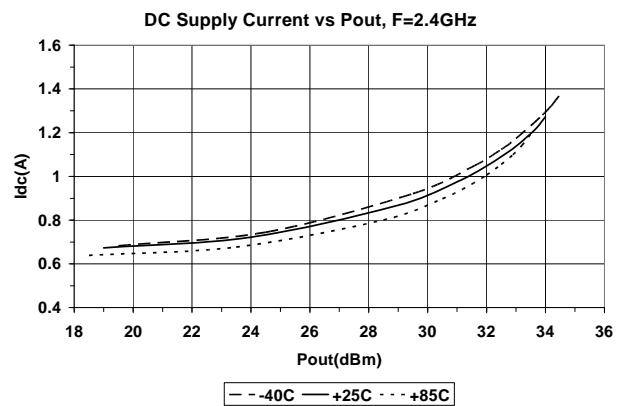
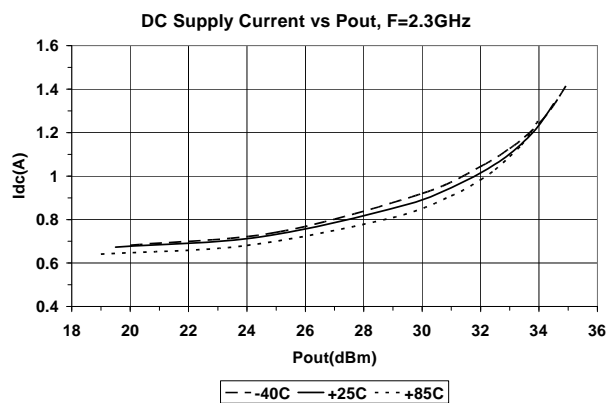
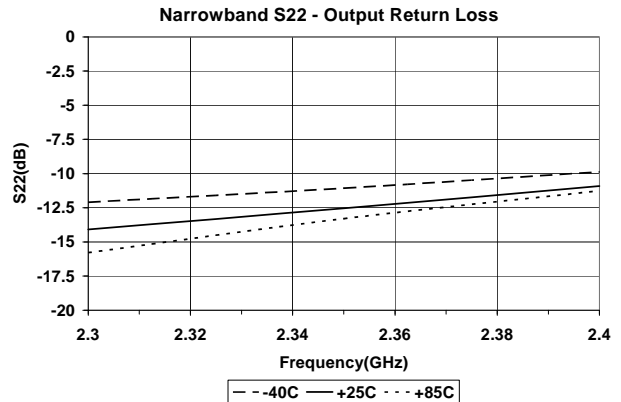
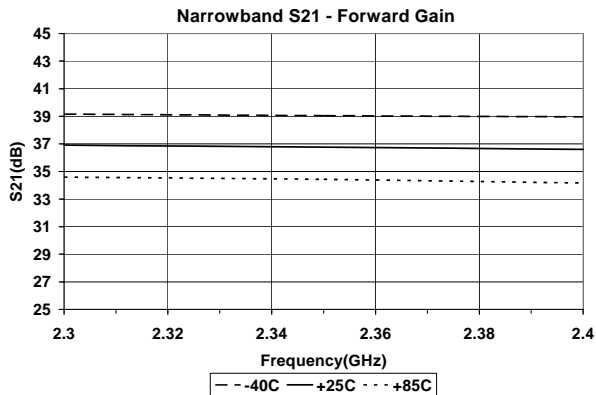
Note 1: Measured with 2.3GHz to 2.4GHz Application circuit

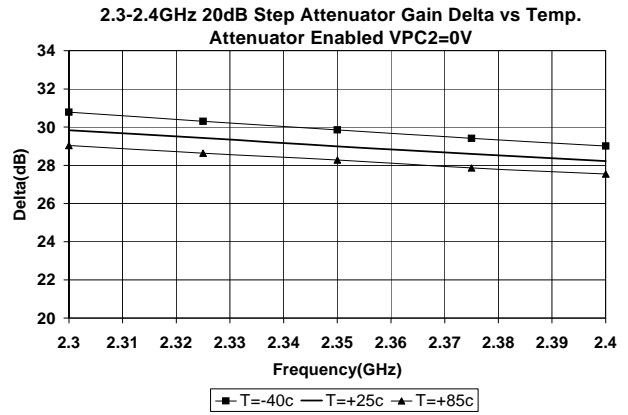
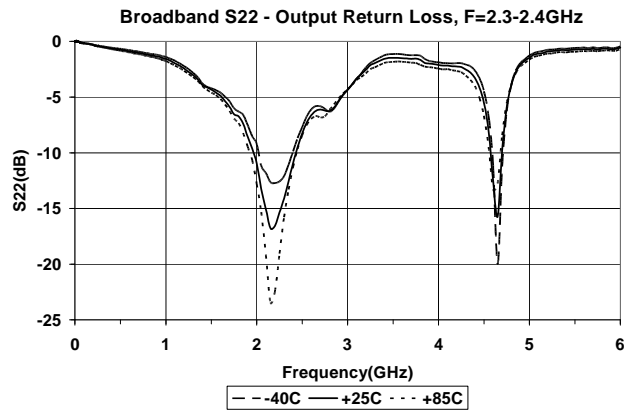
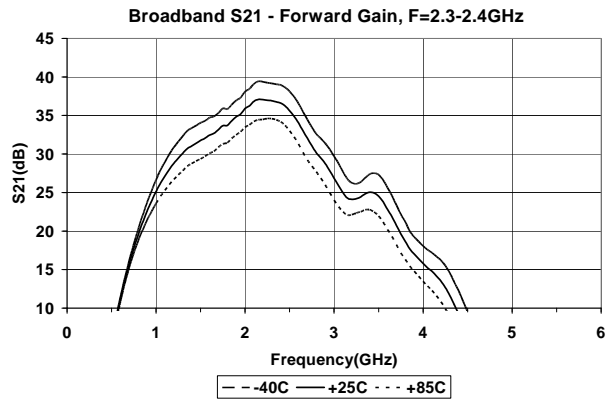
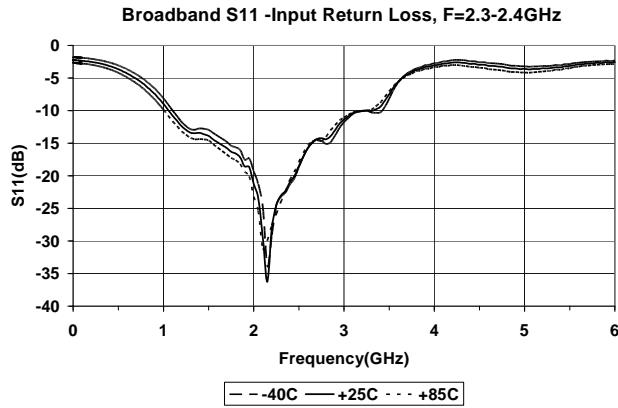
Note 2: Measured with 2.5GHz to 2.7GHz Application circuit

Measured 2.3GHz to 2.4GHz Application Circuit Data ($V_{CC}=V_{PC}=6.0V$, $I_q=653mA$, $T=25^\circ C$)

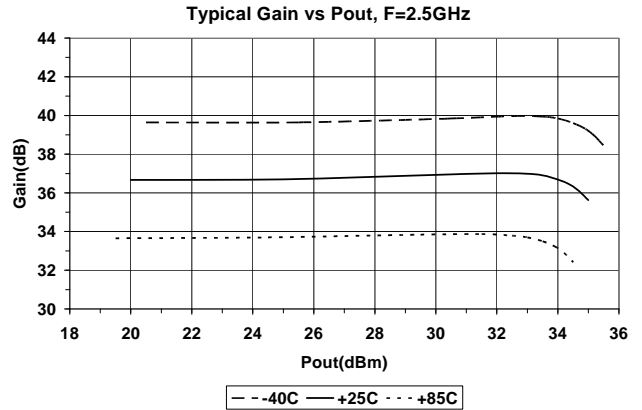
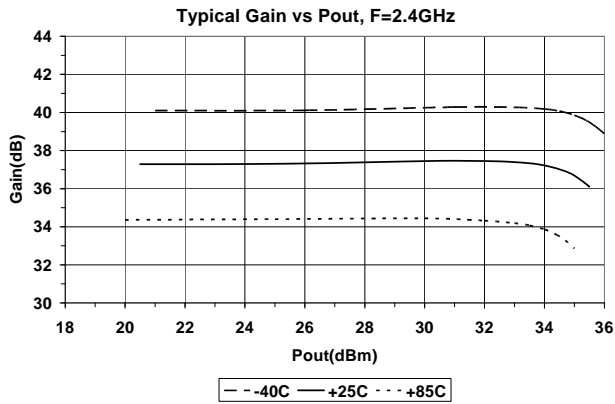
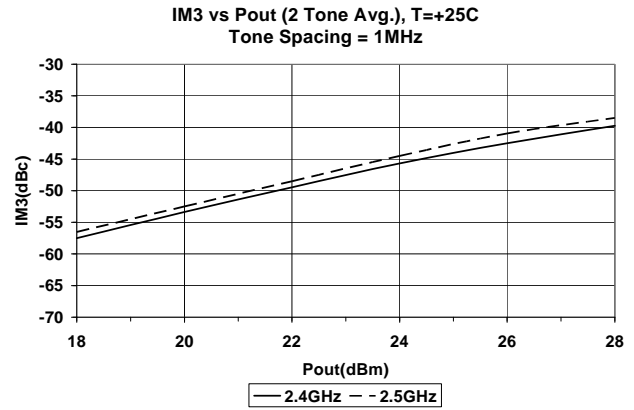
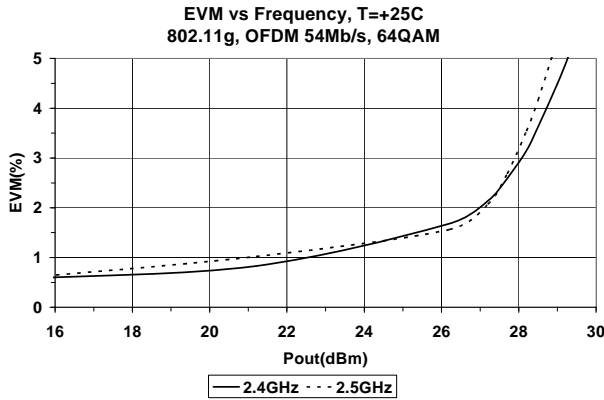
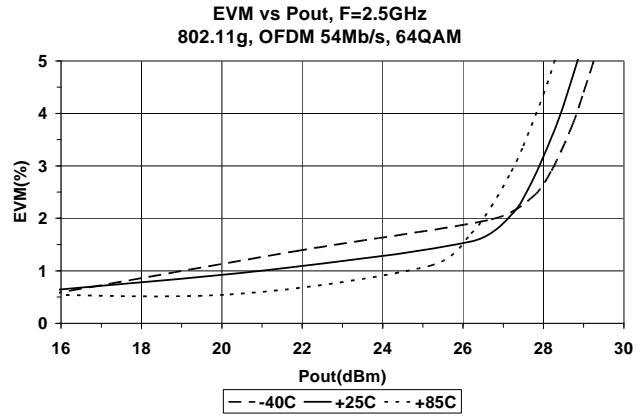
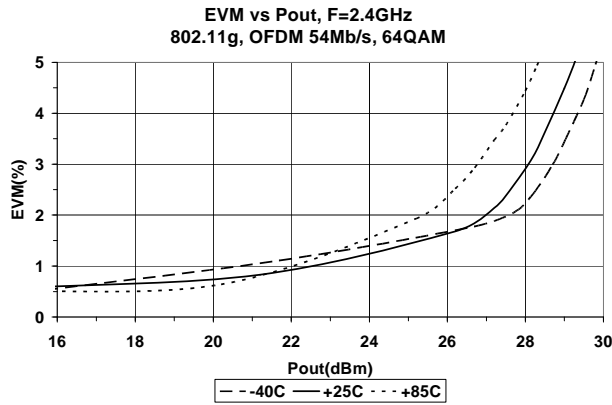


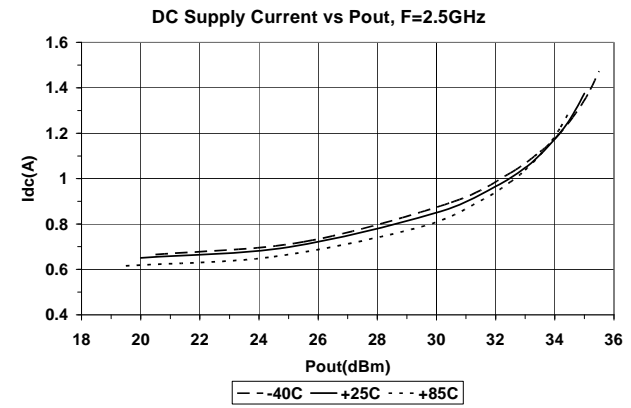
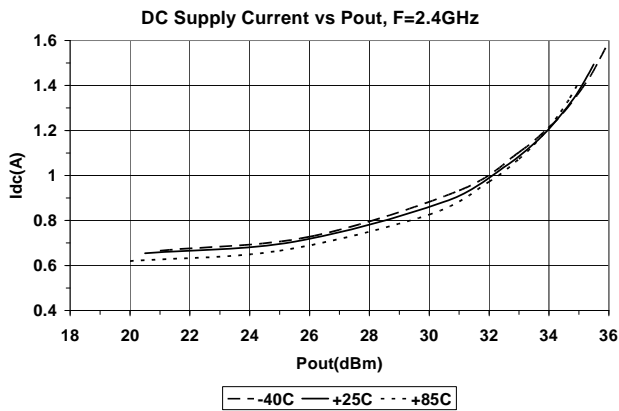
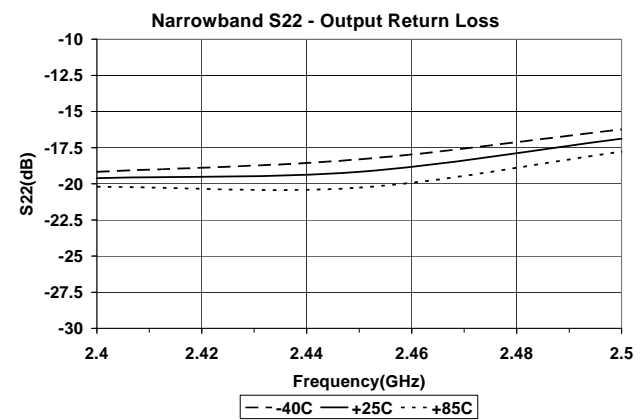
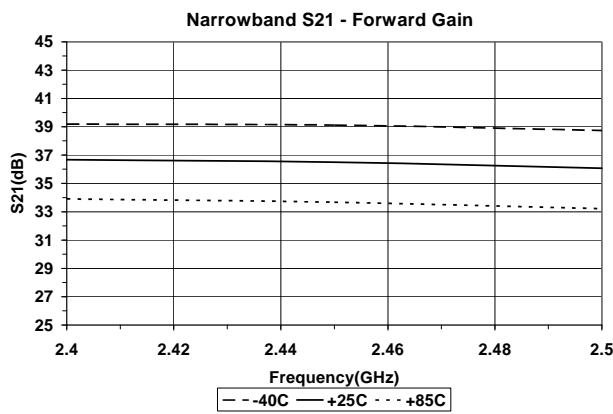
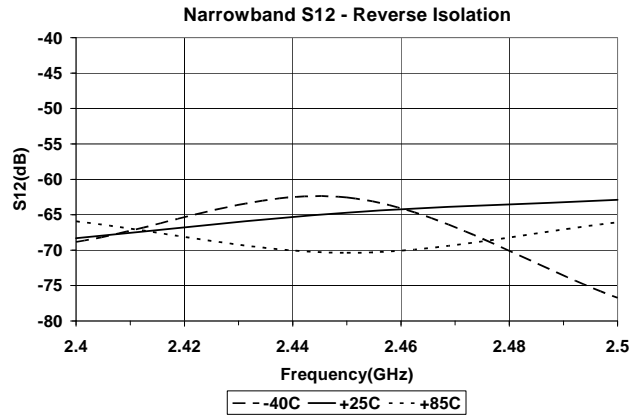
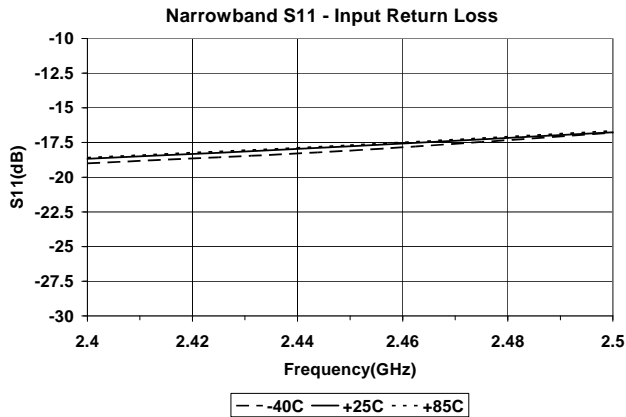


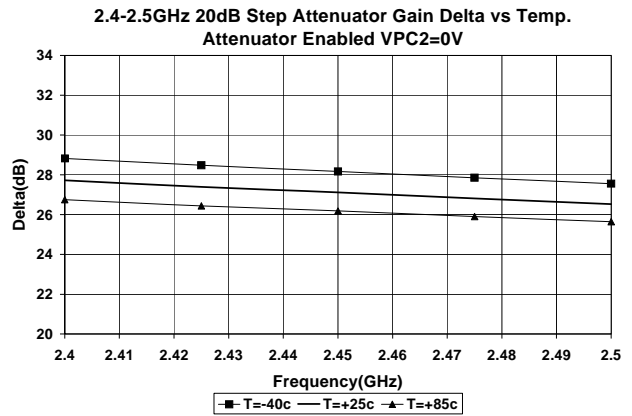
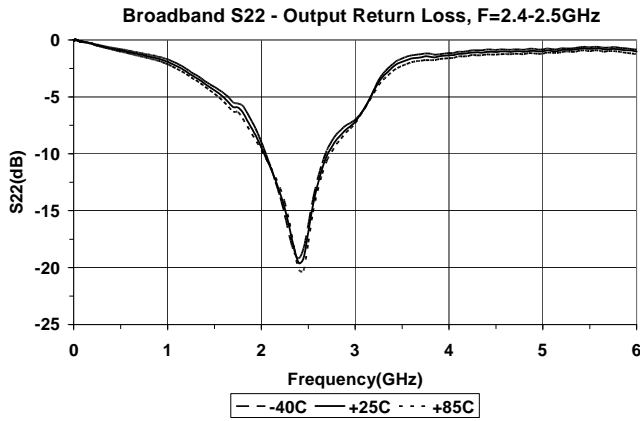
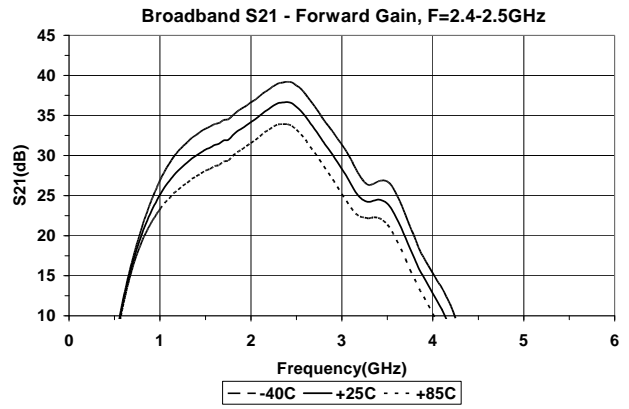
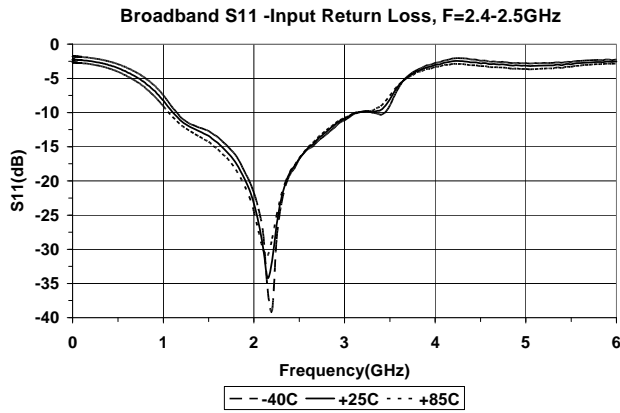
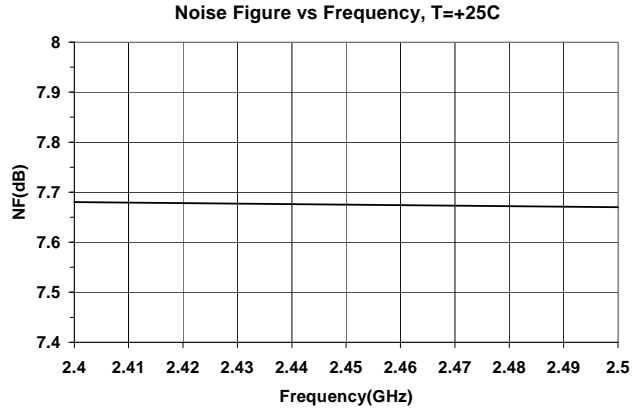
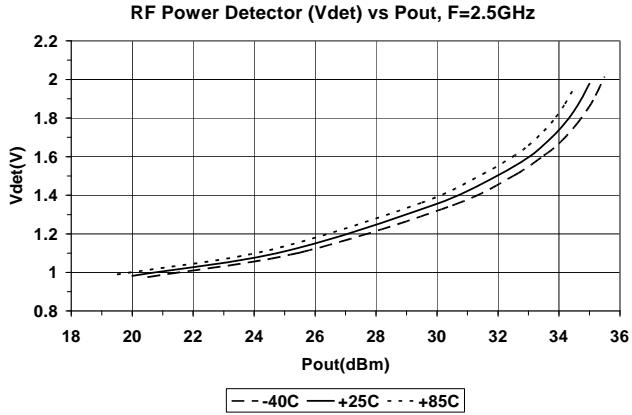




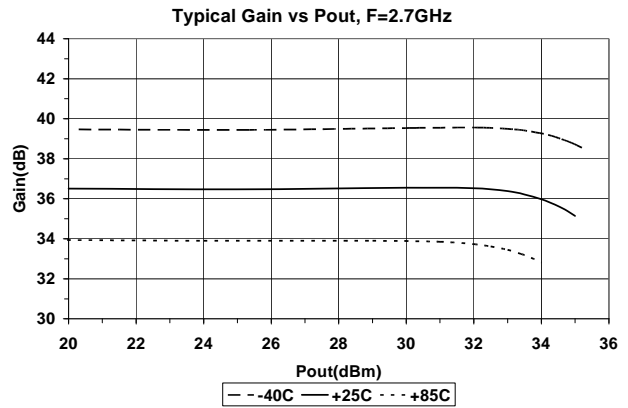
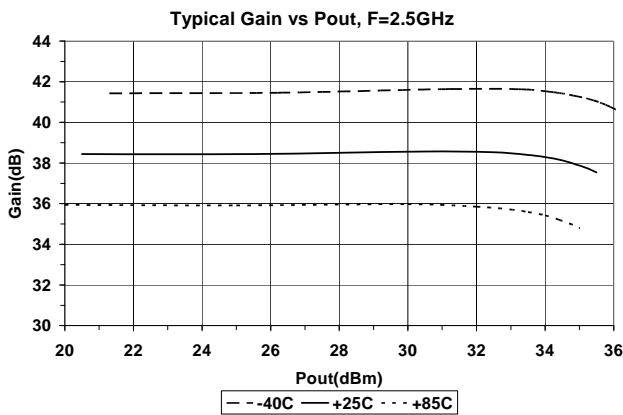
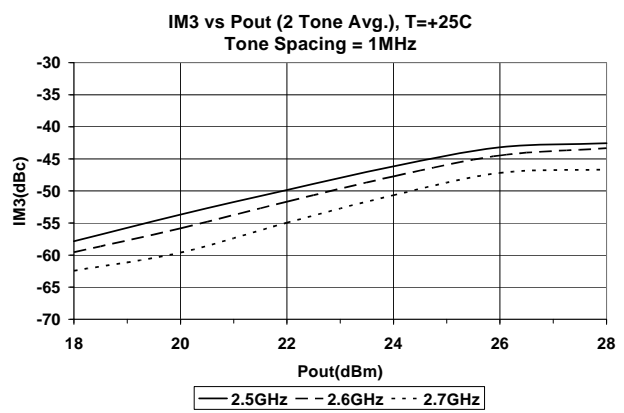
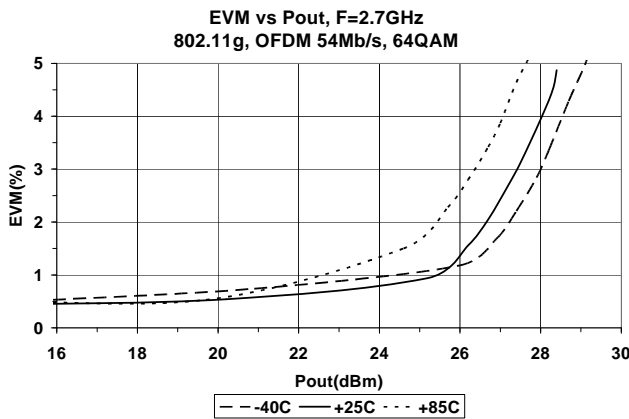
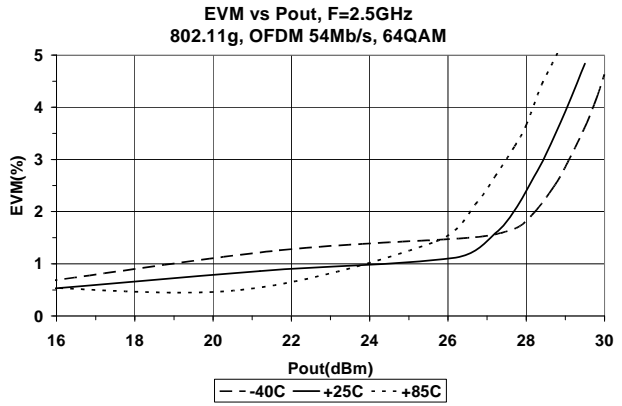
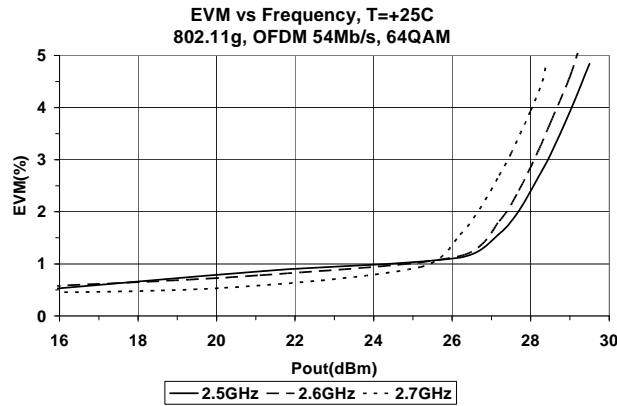
Measured 2.4GHz to 2.5GHz Application Circuit Data ($V_{CC}=V_{PC}=6.0V$, $I_q=653mA$, $T=25^\circ C$)

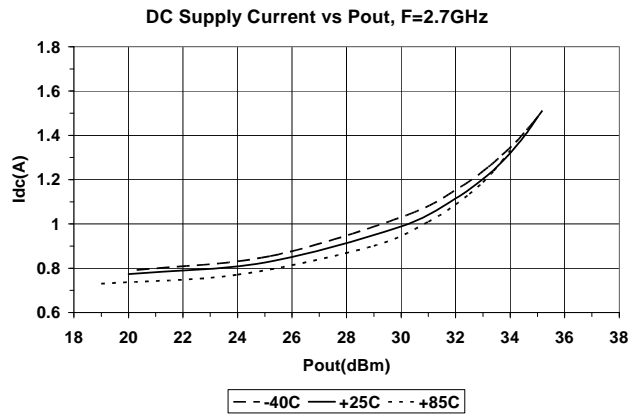
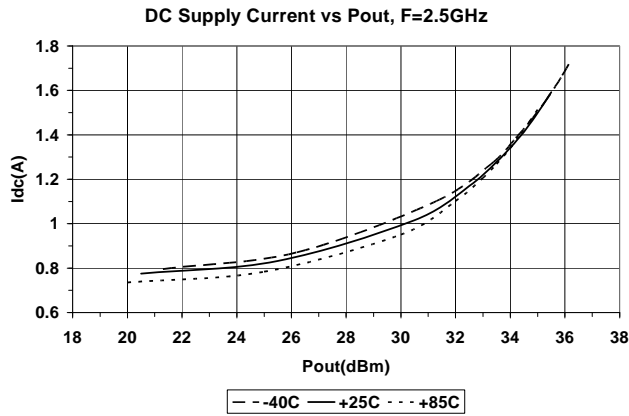
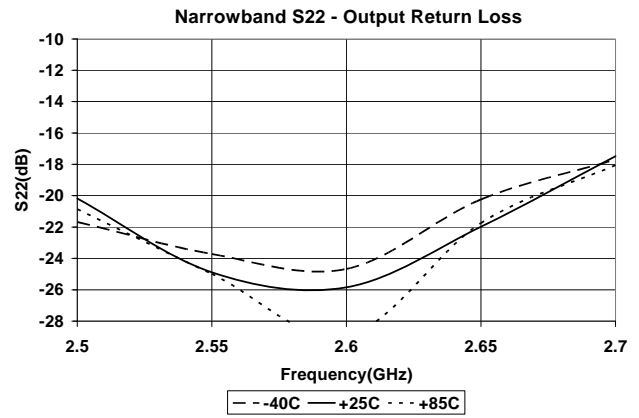
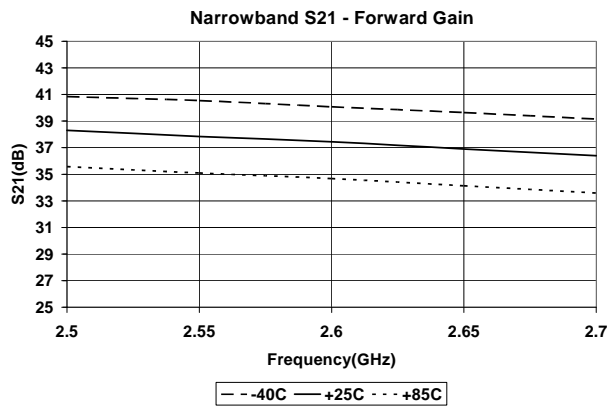
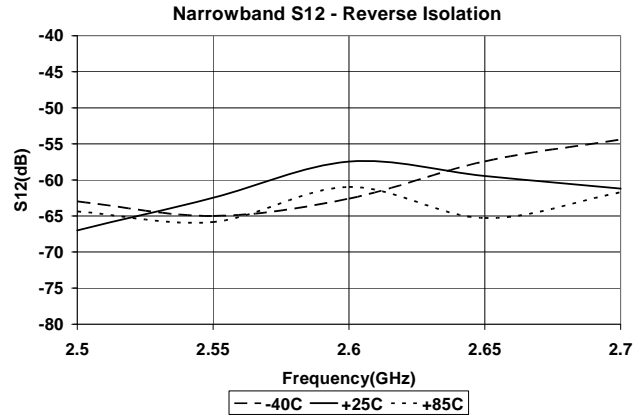
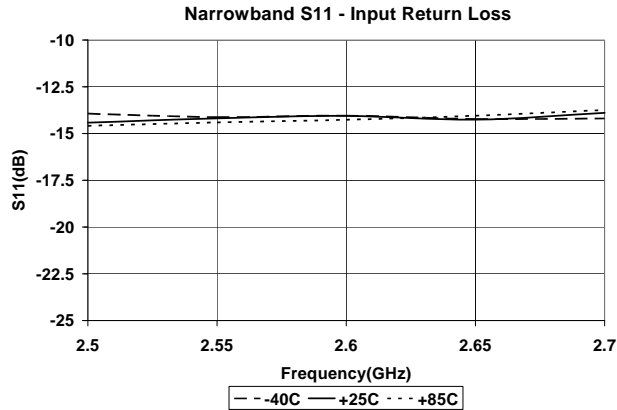




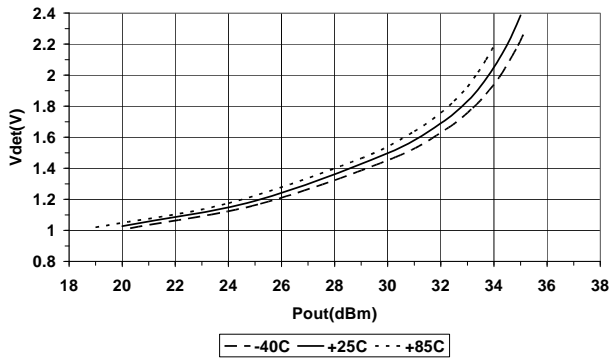


Measured 2.5GHz to 2.7GHz Application Circuit Data ($V_{CC}=V_{PC}=6.0V$, $I_q=724mA$, $T=25^\circ C$)

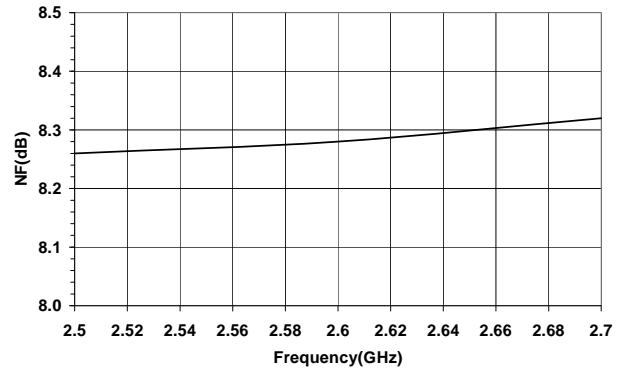




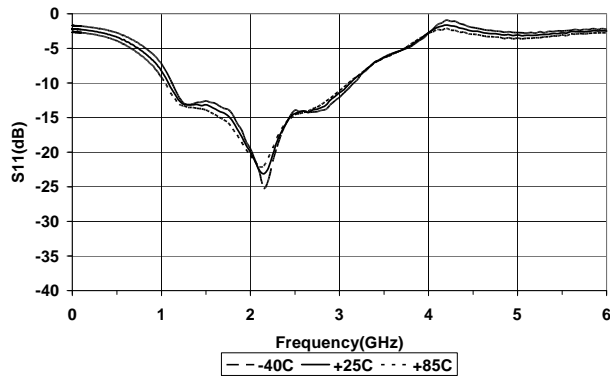
RF Power Detector (Vdet) vs Pout, F=2.7GHz



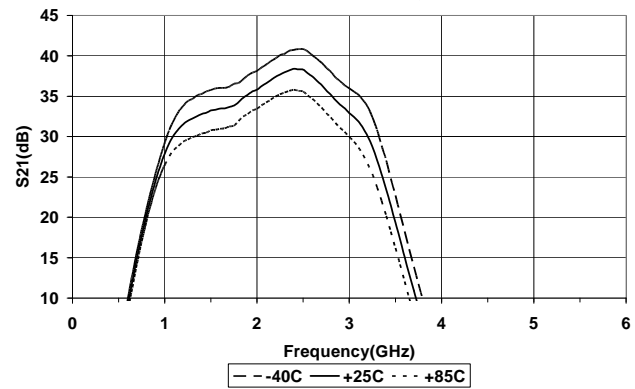
Noise Figure vs Frequency, T=+25C



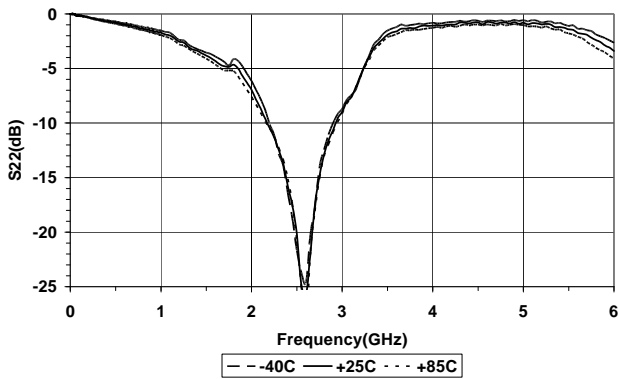
Broadband S11 - Input Return Loss, F=2.5-2.7GHz



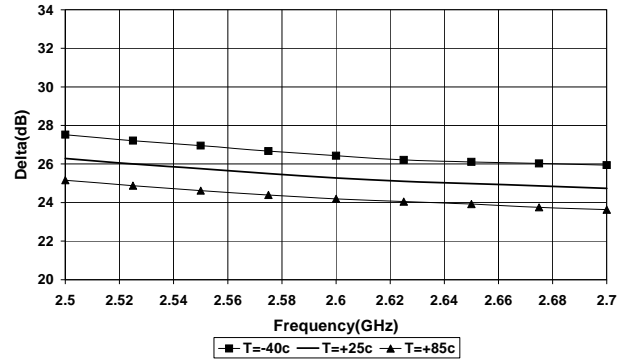
Broadband S21 - Forward Gain, F=2.5-2.7GHz



Broadband S22 - Output Return Loss, F=2.5-2.7GHz



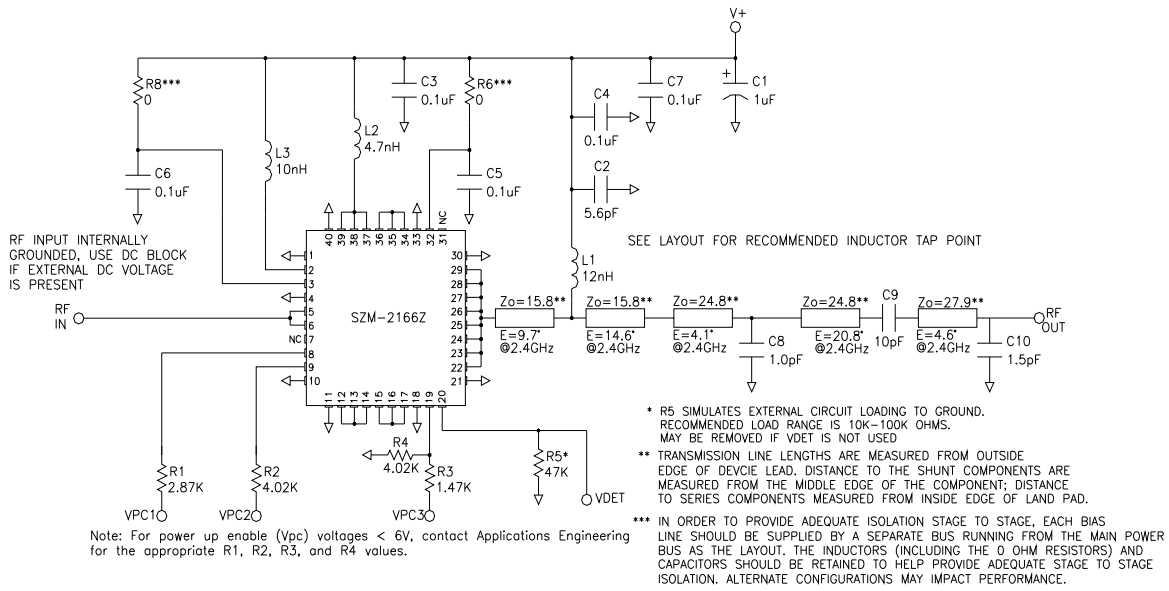
2.5-2.7GHz 20dB Step Attenuator Gain Delta vs Temp. Attenuator Enabled VPC2=0V



| Pin | Function | Description |
|--|--|--|
| 7, 11, 12, 22, 29, 31, 39, 40 | NC | These are no connect (NC) pins and are not wired inside the package. It is recommended to connect them as shown in the application circuit to achieve the stated performance. |
| 1, 10, 21, 30 | GND | These pins are internally grounded inside the package to the backside ground paddle. It is recommended to also ground them externally to the package to achieve the specified performance. |
| 2 | VC1 | This is the collector of the first stage. |
| 3 | VBIAS12 | This is the supply voltage for the active bias circuit of the 1st and 2nd stages. |
| 4-5 | R1A-R2A | A resistor is tied across these pins internal to the package. |
| 6 | RF IN | This is the RF input pin. It is DC grounded inside the package. Do not apply DC voltage to this pin. |
| 8 | VPC1 | Power up/down control pin for the 1st stage. An external series resistor is required for proper setting of bias levels depending on control voltage. The voltage of this pin should never exceed the voltage on pin 3 by more than 0.5V unless the supply current from pin 3 is limited <10mA. |
| 9 | VPC2 | Power up/down control pin for the 2nd stage. Power down VPC<1V for step attenuator function enable. An external series resistor is required for proper setting of bias levels depending on control voltage. The voltage on this pin should never exceed the voltage on pin 3 by more than 0.5V unless the supply current from pin 3 is limited<10mA. |
| 13, 38 | VC2A, VC2B | These two pins are connected internal to the package and connect to the 2nd stage collector. To achieve specified performance, the layout of these pins should match the Recommended Land Pattern. |
| 14-15 17-18 33-34 36-37 | C1A-C2A C3A-C4A C4B-C3B C2B-C1B | These pins have capacitors across them internal to the package as shown in the below schematic. They are used as tuning and RF coupling elements between the 2nd and 3rd stage. |
| 16, 35 | VB3A, VB3B | These are the connections to the base of the 3rd stage output device. To achieve specified performance, the layout of these pins should match the Recommended Land Pattern. |
| 19 | VPC3 | Power up/down control pin for the 2nd stage. An external series resistor is required for proper setting of bias levels depending on control voltage. The voltage on this pin should never exceed the voltage on pin 32 by more than 0.5V unless the supply current from pin 33 is limited <10mA. |
| 20 | VDET | This is the output port for the power detector. It samples the power at the input of the 3rd stage. |
| 23-28 | RF OUT | These are the RF output pins and DC connections to the 3rd stage collector. |
| 32 | VBIAS3 | This is the supply voltage for the active bias circuit of the 3rd stage. |

2.3GHz to 2.4GHz Evaluation Board Schematic

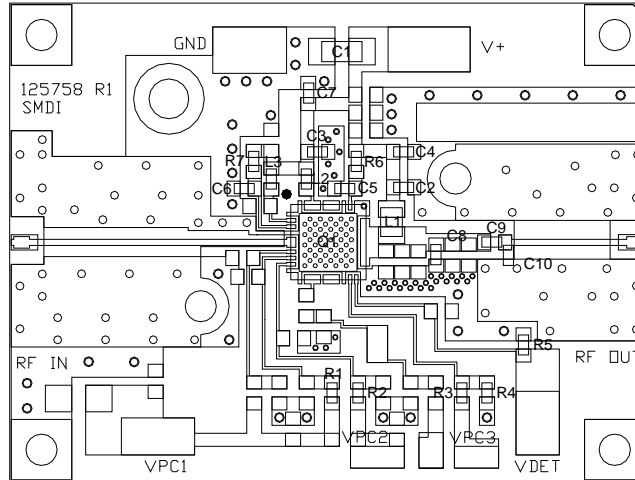
$$V_{CC}=V+=V_{PC}=6.0V$$



2.3GHz to 2.4GHz Evaluation Board Layout

$V_{CC}=V+=V_{PC}=6.0V$

Board material GETEK, 10mil thick, Dk=3.9, 2oz copper

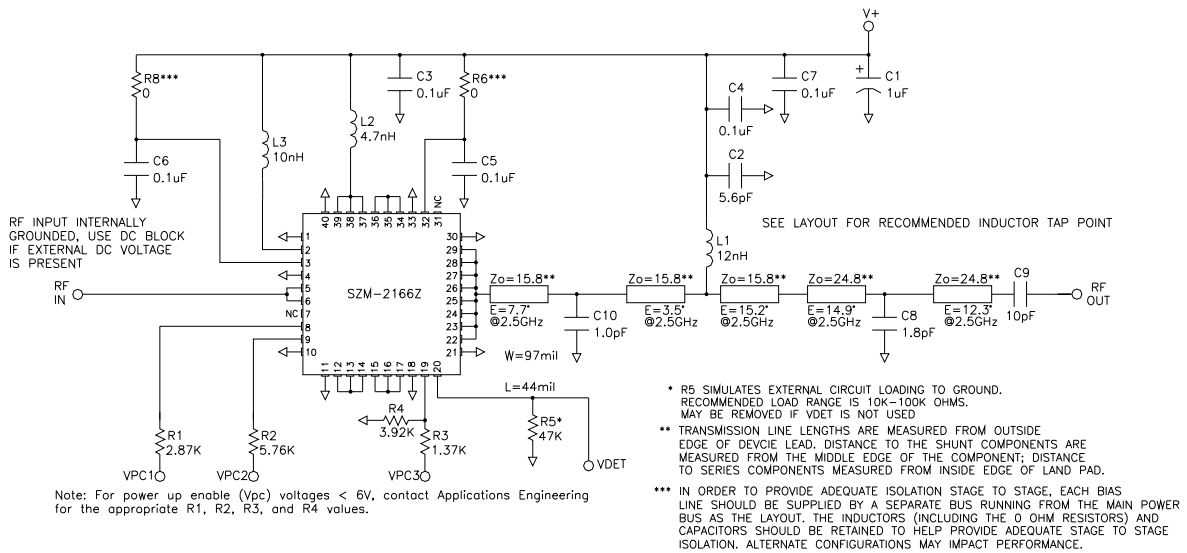


Bill of Materials

| DESG | Description | Notes |
|----------------|--------------------------|---|
| Q1 | SZM-2166Z | 6mmx6mm QFN |
| R1 | 2.87K Ω , 0603 1% | 0402 may be used. |
| R2, 4 | 4.02K Ω , 0603 1% | 0402 may be used. |
| R3 | 1.47K Ω , 0603 1% | 0402 may be used. |
| R5 | 47K Ω , 0603 | 0402 may be used. |
| R6, 7 | 0 Ω , 0603 | 0402 may be used. |
| C1 | 1uF 16V MLCC CAP | Tantalum ok for EVM performance. Use MLCC type for best IM3 levels. |
| C2 | 5.6pF CAP, 0603 | NPO ROHM MCH185A5R6DK or equiv. |
| C3, 4, 5, 6, 7 | 0.1uF CAP, 0603 | X7R 0402 ok, ROHM MCH182CN104K or equiv. |
| C8 | 1.0pF CAP, 0603 | NPO, low ESR, ATC 600S1R0CW250 or equiv. |
| C9 | 10pF CAP, 0603 | NPO, low ESR, ATC 600S100JW250 or equiv. |
| C10 | 1.5pF CAP, 0603 | NPO, low ESR, ATC 600S1R5JW250 or equiv. |
| L1 | 12nH IND 0805 | Coilcraft 0805HQ - 12NXJBB |
| L2 | 4.7nH IND, 0603 | TOKO 0603 - LL1608FH4N7J |
| L3 | 10nH IND, 0603 | TOKO 0603 - LL1608FH10NJ |

2.4GHz to 2.5GHz Evaluation Board Schematic

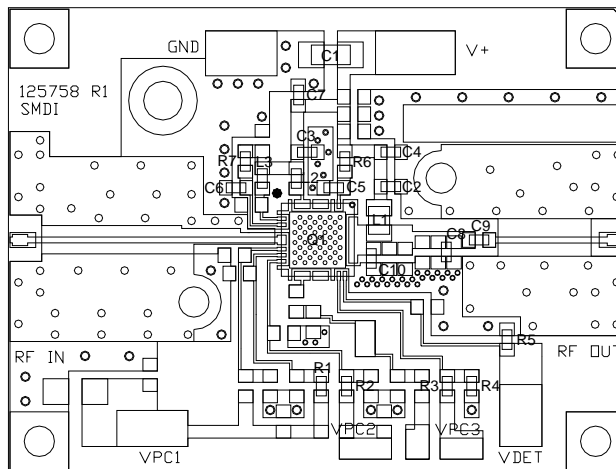
$$V_{CC}=V+=V_{PC}=6.0V$$



2.4GHz to 2.5GHz Evaluation Board Layout

$V_{CC}=V+=V_{PC}=6.0V$

Board material GETEK, 10mil thick, Dk=3.9, 2oz copper

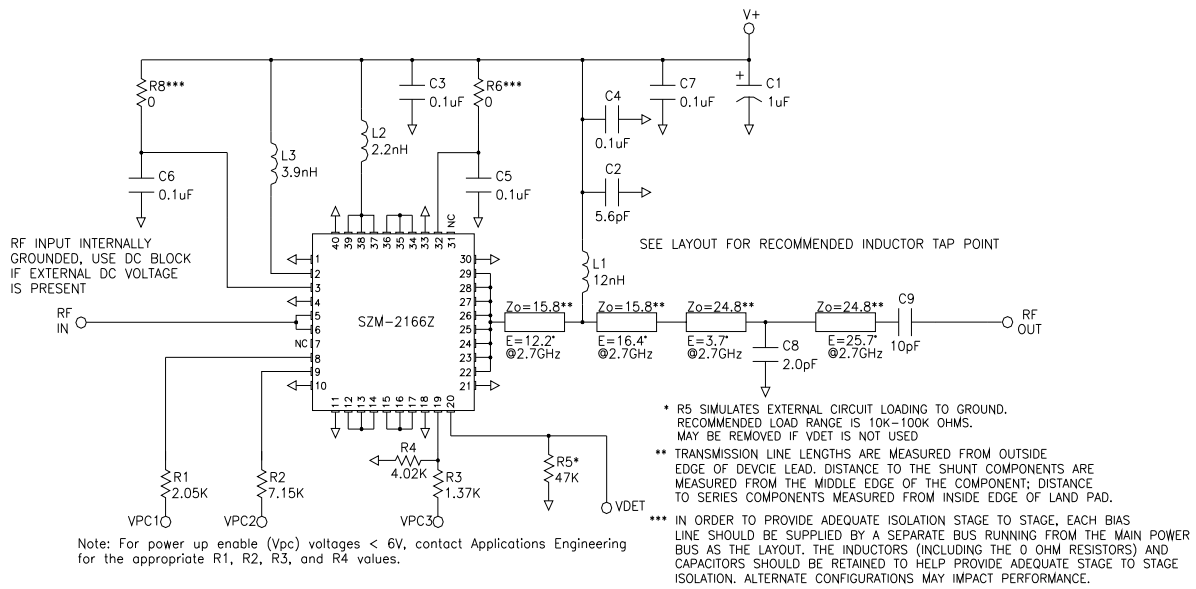


Bill of Materials

| DESG | Description | Notes |
|----------------|--------------------------|---|
| Q1 | SZM-2166Z | 6mmx6mm QFN |
| R1 | 2.87K Ω , 0603 1% | 0402 may be used. |
| R2 | 5.76K Ω , 0603 1% | 0402 may be used. |
| R3 | 1.37K Ω , 0603 1% | 0402 may be used. |
| R4 | 3.92K Ω , 0603 1% | 0402 may be used. |
| R5 | 47K Ω , 0603 | 0402 may be used. |
| R6, 7 | 0 Ω , 0603 | 0402 may be used. |
| C1 | 1uF 16V MLCC CAP | Tantulum ok for EVM performance. Use MLCC type for best IM3 levels. |
| C2 | 5.6pF CAP, 0603 | NPO ROHM MCH185A5R6DK or equiv. |
| C3, 4, 5, 6, 7 | 0.1uF CAP, 0603 | X7R 0402 ok, ROHM MCH182CN104K or equiv. |
| C8 | 1.8pF CAP, 0603 | NPO, low ESR, ATC 600S1R8CW250 or equiv. |
| C9 | 10pF CAP, 0603 | NPO, low ESR, ATC 600S100JW250 or equiv. |
| C10 | 1.0pF CAP, 0603 | NPO, low ESR, ATC 600S1R0JW250 or equiv. |
| L1 | 12nH IND 0805 | Coilcraft 0805HQ - 12NXJBB |
| L2 | 4.7nH IND, 0603 | TOKO 0603 - LL1608FH4N7J |
| L3 | 10nH IND, 0603 | TOKO 0603 - LL1608FH10NJ |

2.5GHz to 2.7GHz Evaluation Board Schematic

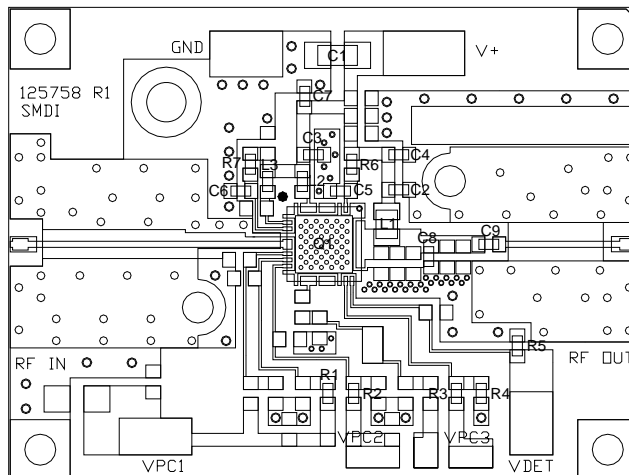
$$V_{CC}=V+=V_{PC}=6.0V$$



2.5GHz to 2.7GHz Evaluation Board Layout

$V_{CC}=V+=V_{PC}=6.0V$

Board material GETEK, 10mil thick, Dk=3.9, 2oz copper



Bill of Materials

| DESG | Description | Notes |
|----------------|--------------------------|---|
| Q1 | SZM-2166Z | 6mmx6mm QFN |
| R1 | 2.05K Ω , 0603 1% | 0402 may be used. |
| R2 | 4.99K Ω , 0603 1% | 0402 may be used. |
| R3 | 1.37K Ω , 0603 1% | 0402 may be used. |
| R4 | 4.02K Ω , 0603 1% | 0402 may be used. |
| R5 | 47K Ω , 0603 | 0402 may be used. |
| R6, 7 | 0 Ω , 0603 | 0402 may be used. |
| C1 | 1uF 16V MLCC CAP | Tantulum ok for EVM performance. Use MLCC type for best IM3 levels. |
| C2 | 5.6pF CAP, 0603 | NPO ROHM MCH185A5R6DK or equiv. |
| C3, 4, 5, 6, 7 | 0.1uF CAP, 0603 | X7R 0402 ok, ROHM MCH182CN104K or equiv. |
| C8 | 2.0pF CAP, 0603 | NPO, low ESR, ATC 600S2ROCW250 or equiv. |
| C9 | 10pF CAP, 0603 | NPO, low ESR, ATC 600S100JW250 or equiv. |
| L1 | 12nH IND 0805 | Coilcraft 0805HQ - 12NXJBB |
| L2 | 2.2nH IND, 0603 | TOKO 0603 - LL1608FH2N2J |
| L3 | 3.9nH IND, 0603 | TOKO 0603 - LL1608FH3N9J |

Ordering Information

| Ordering Code | Description |
|------------------|---|
| SZM2166ZSQ | Standard 25 piece bag |
| SZM2166ZSR | Standard 100 piece reel |
| SZM2166Z | Standard 1000 piece reel |
| SZM2166ZPCK-EVB1 | Evaluation Board 2.3GHz to 2.4 GHz Tune and 5 loose sample pieces |
| SZM2166ZPCK-EVB2 | Evaluation Board 2.4GHz to 2.5GHz Tune and 5 loose sample pieces |
| SZM2166ZPCK-EVB3 | Evaluation Board 2.5GHz to 2.7 GHz Tune and 5 loose sample pieces |



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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